Abstract

In search of opto-electronic nano materials, we often come across Gallium Nitride nanotubes (GaN-NT) with excellent electrical and optical characteristics. Gallium Nitride nanotubes are predominantly semiconducting and have been less explored in its application as a transistor channel through Density Functional Theory (DFT). Comparing Gallium Nitride nanotubes with Boron Nitride nanotubes (BN-NT) and Carbon nanotubes (CNT), we have obtained distinguishing features of Gallium Nitride nanotubes. In this work, Transistor simulation with Gallium Nitride nanotubes has been reported with the nanotube as channel. Properties of various configurations of nanotubes are compared among Carbon, Boron Nitride and Gallium Nitride nanotubes.

References

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Gallium Nitride Nanotube and its Application as Transistors


Index Terms

Computer Science
Applied Sciences

Keywords

Gallium Nitride Nanotubes  Gan Nanotube Transistor  Density Functional Theory (dft)
Bond Rotation

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